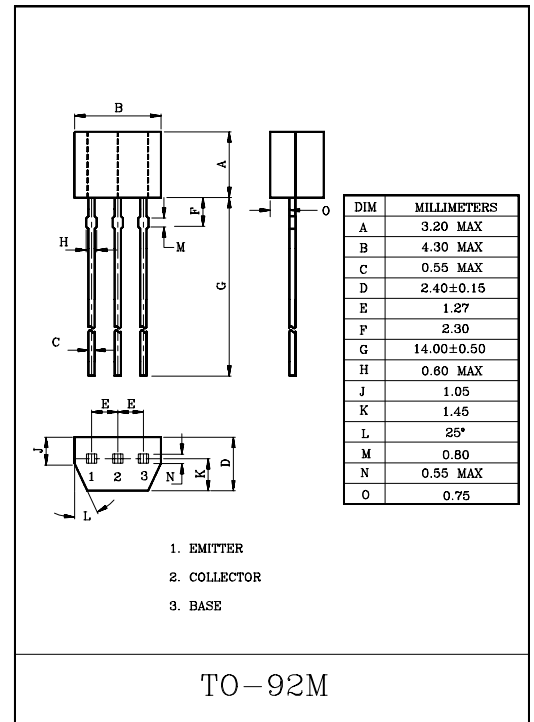
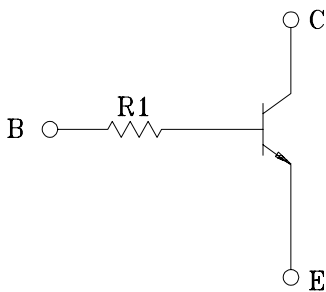


SWITCHING APPLICATION.
INTERFACE CIRCUIT AND DRIVER CIRCUIT APPLICATION.

FEATURES

- With Built-in Bias Resistors.
- Simplify Circuit Design.
- Reduce a Quantity of Parts and Manufacturing Process.

EQUIVALENT CIRCUIT



MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	100	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

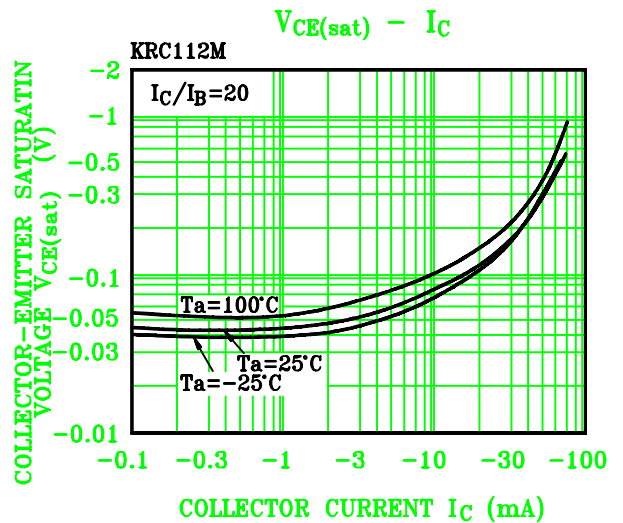
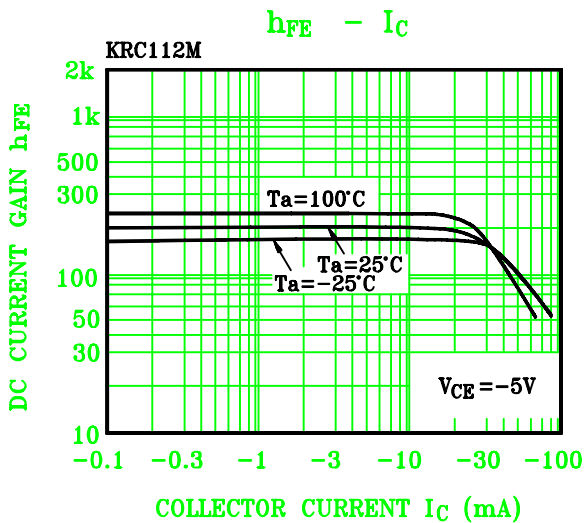
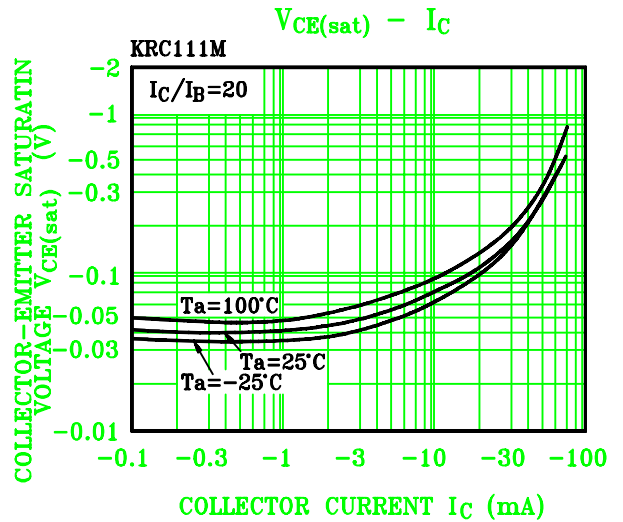
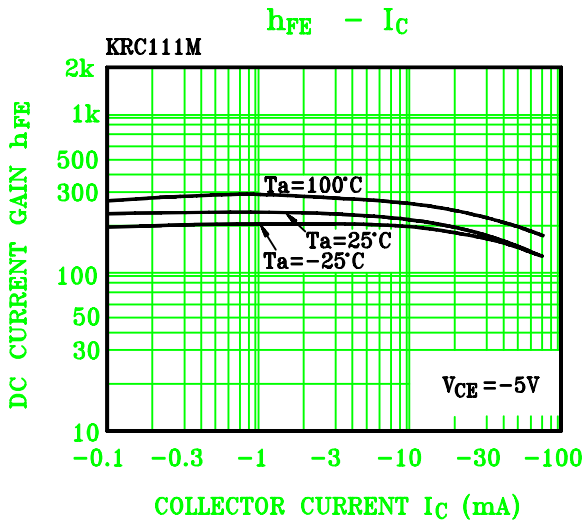
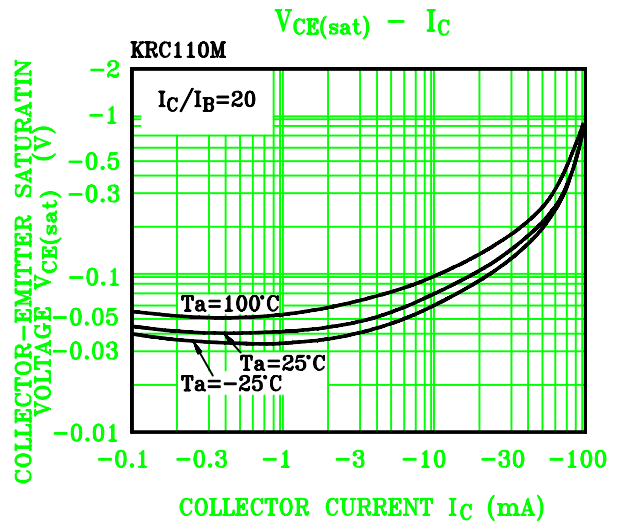
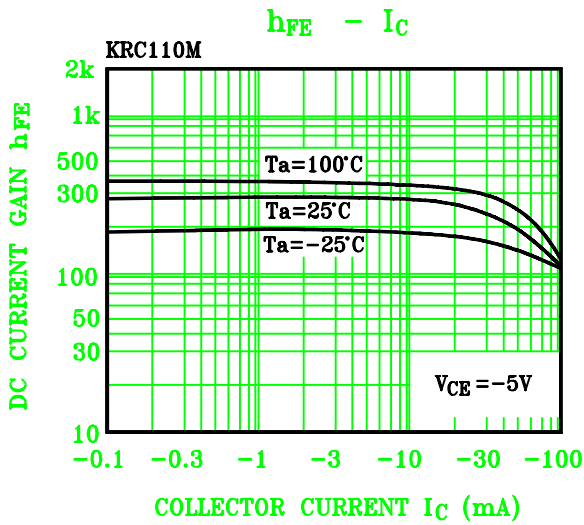
KRC110M ~ KRC114M

ELECTRICAL CHARACTERISTICS (T_a=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current		I _{CBO}	V _{CB} =50V, I _B =0	-	-	100	nA	
Emitter Cut-off Current		I _{EBO}	V _{EB} =5V, I _C =0	-	-	100	nA	
DC Current Gain		h _{FE}	V _{CE} =5V, I _C =1mA	120	-	-		
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =10mA, I _B =0.5mA	-	0.1	0.3	V	
Transition Frequency		f _T *	V _{CE} =10V, I _C =5mA	-	250	-	MHz	
Input Resistor	KRC110M	R _i		-	4.7	-	kΩ	
	KRC111M			-	10	-		
	KRC112M			-	100	-		
	KRC113M			-	22	-		
	KRC114M			-	47	-		
Switching Time	Rise Time	t _r	V _O =5V V _{IN} =5V R _L =1kΩ	-	0.025	-	μS	
				KRC111M	-	0.03		-
				KRC112M	-	0.3		-
				KRC113M	-	0.06		-
				KRC114M	-	0.11		-
	Storage Time	t _{stg}		KRC110M	-	3.0		-
				KRC111M	-	2.0		-
				KRC112M	-	6.0		-
				KRC113M	-	4.0		-
				KRC114M	-	5.0		-
	Fall Time	t _f		KRC110M	-	0.2		-
				KRC111M	-	0.12		-
				KRC112M	-	2.0		-
				KRC113M	-	0.9		-
				KRC114M	-	1.4		-

Note : *Characteristic of Trnsistor Only

KRC110M ~ KRC114M



KRC110M ~ KRC114M

